

International IOR Rectifier

IRKT152/04

THYRISTOR/ THYRISTOR

INT-A-pak™ Power Module

Features

- Electrically Isolated by DBC Ceramic (Al_2O_3)
- 3500 V_{RMS} Isolating Voltage
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Simple Mounting
- UL under approval

150 A

Applications

- Battery Charges
- Welders
- Power Converters

Major Ratings and Characteristics

Parameters	IRKT152/04	Units
$I_{\text{T(AV)}}$	150	A
@ T_{C}	85	°C
$I_{\text{T(RMS)}}$	330	A
I_{TSM} @ 50Hz	4000	KA ² s
@ 60Hz	4200	
i^2t @ 50Hz	80	
@ 60Hz	73	
$i^2\sqrt{t}$	800	KA ² /s
V_{RRM}	400	V
T_{STG} range	-40 to 150	°C
T_{J} range	-40 to 125	

CASE STYLE NEW INT-A-PAK



ELECTRICAL SPECIFICATIONS**Voltage Ratings**

Type number	V_{RRM}/V_{DRM} , Maximum repetitive peak reverse voltage V	V_{RSM}/V_{DSM} , Maximum non-repetitive peak reverse voltage V	I_{RRM}/I_{DRM} @ 125°C mA
IRKT152/04	400	500	50

On-state Conduction

Parameter	IRKT152/04	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Case temperature	150	A	180° conduction half sine wave
	85	°C	
$I_{T(RMS)}$ Maximum RMS on-state current	330	A	as AC switch
I_{TSM} Maximum peak, one-cycle on-state, non-repetitive surge current	4000	A	t = 10ms No voltage
	4200		t = 8.3ms reapplied
	3350		t = 10ms 100% V_{RRM}
	3500		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	80	KA ² s	t = 10ms No voltage
	73		t = 8.3ms reapplied
	56		t = 10ms 100% V_{RRM}
	51		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	800	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)}$ Value of threshold voltage	0.82	V	@ T_J max.
r_t On-state slope resistance	1.44	mΩ	
V_{TM} Maximum on-state voltage drop	1.44	V	$I_{pk} = 470A$, $T_J = 25^\circ C$
I_H Maximum Holding Current	200	mA	$T_J = 25^\circ C$, anode supply = 6V, resistive load, gate open circuit
I_L Maximum Latching Current	400		$T_J = 25^\circ C$, anode supply = 6V, resistive load

Switching

t _{gd}	Typical delay time	1	μs	T _J = 25°C	Gate Current=1A dI _g /dt=1A/μs
t _{gr}	Typical rise time	2		T _J = 25°C	V _d =0,67% V _{DRM}
t _q	Typical turn-off time	50 - 200		I _{TM} = 300 A; -dI/dt = 15 A/μs; T _J = T _J max V _r = 50 V; dV/dt = 20 V/μs; Gate 0 V, 100Ω	

Blocking

I_{RRM} Maximum peak reverse and	50	mA	$T_J = 125^\circ C$
I_{DRM} off-state leakage current			
V_{INS} RMS isolation voltage	3500	V	50Hz, circuit to base, all terminals shorted, t = 1s
dV/dt critical rate of rise of off-state voltage	1000	V/μs	$T_J = T_J \text{ max.}$, exponential to 67% rated V_{DRM}

Triggering

Parameter	IRKT152/04	Units	Conditions
P_{GM} Max. peak gate power	12	W	$t_p \leq 5ms, T_J = T_{Jmax}$.
$P_{G(AV)}$ Max. average gate power	3	W	$f=50Hz, T_J = T_{Jmax}$.
I_{GM} Max. peak gate current	3	A	$t_p \leq 5ms, T_J = T_{Jmax}$.
$-V_{GT}$ Max. peak negative gate voltage	10	V	
V_{GT} Max. required DC gate voltage to trigger	4	V	$T_J = -40^\circ C$ Anode supply = 6V, resistive load; $R_a = 1\Omega$
	2.5		$T_J = 25^\circ C$
	1.7		$T_J = T_{Jmax}$.
I_{GT} Max. required DC gate current to trigger	270	mA	$T_J = -40^\circ C$ Anode supply = 6V, resistive load; $R_a = 1\Omega$
	150		$T_J = 25^\circ C$
	80		$T_J = T_{Jmax}$.
V_{GD} Max. gate voltage that will not trigger	0.3	V	@ $T_J = T_{Jmax}$., rated V_{DRM} applied
I_{GD} Max. gate current that will not trigger	10	mA	
di/dt Max. rate of rise of turned-on current	300	A/ μs	@ $T_J = T_{Jmax}$., $I_{TM} = 400A$ rated V_{DRM} applied

Thermal and Mechanical Specifications

Parameter	IRKT152/04	Units	Conditions
T_J Max. junction operating temperature range	-40 to 125	$^\circ C$	
T_{slg} Max. storage temperature range	-40 to 150	$^\circ C$	
R_{thJC} Max. thermal resistance, junction to case	0.18	K/W	DC operation, per junction
R_{thCS} Max. thermal resistance, case to heatsink	0.05	K/W	Mounting surface smooth, flat and greased Per module
T Mounting IAP to heatsink torque $\pm 10\%$ busbar to IAP	4 to 6	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.
wt Approximate weight	200 (7.1)		
Case Style	New Int-A-Pak		

ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Devices	Sinusoidal conduction @ T_J max.					Rectangular conduction @ T_J max.					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
IRKT152/04	0.007	0.010	0.013	0.016	0.017	0.009	0.012	0.014	0.016	0.017	K/W

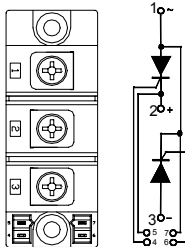
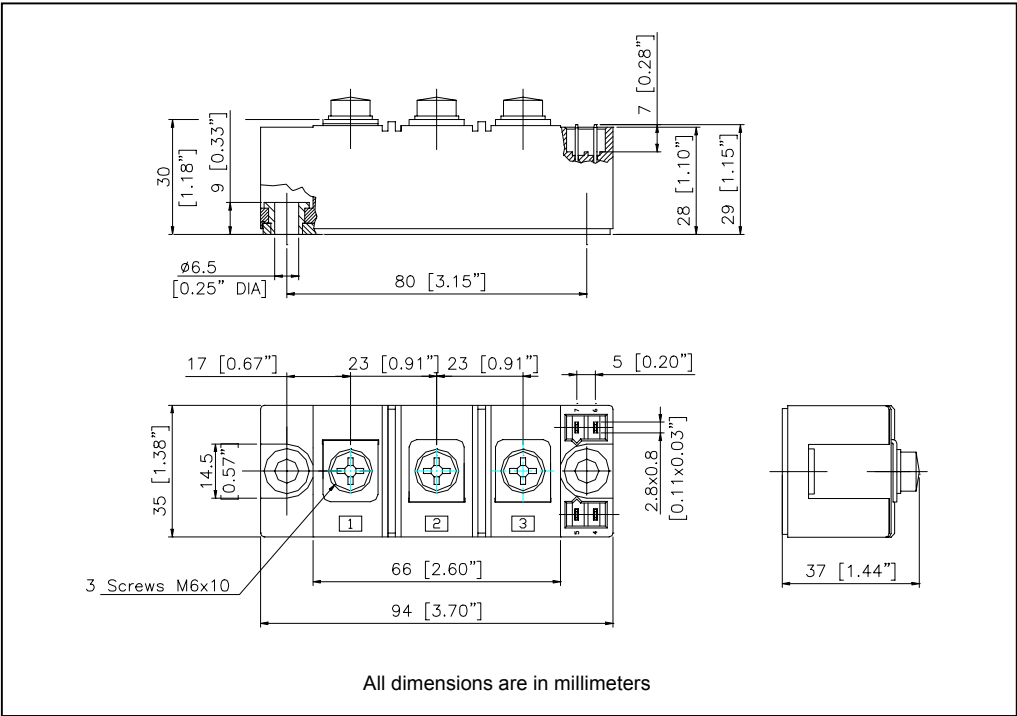
IRKT152/04

Bulletin I27122 rev. B 03/02

Ordering Information Table

Device Code				
IRK	T	152	/	04
1	2	3		4
1	- Module Type			
2	- Circuit Configuration			
3	- Current Rating: $I_{T(AV)}$			
4	- Voltage Code: Code x 100 = V_{RRM}			

Outline Table



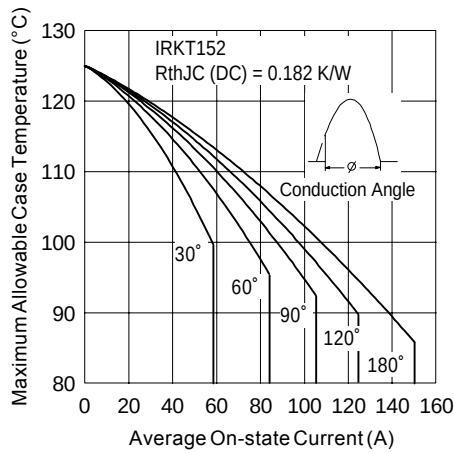


Fig. 1 - Current Ratings Characteristics

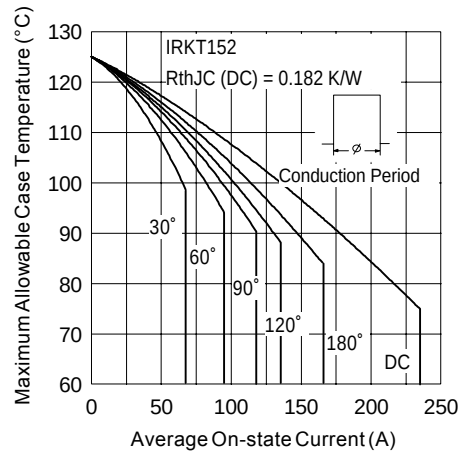


Fig. 2 - Current Ratings Characteristics

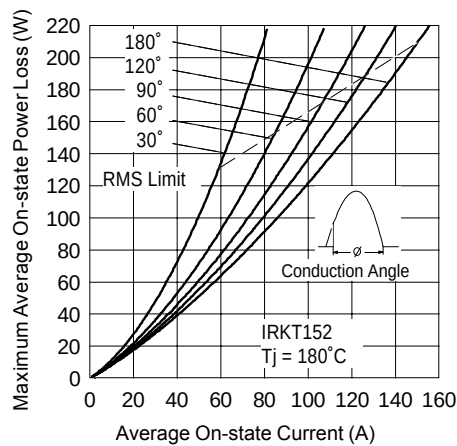


Fig. 3 - Forward Power Loss Characteristics

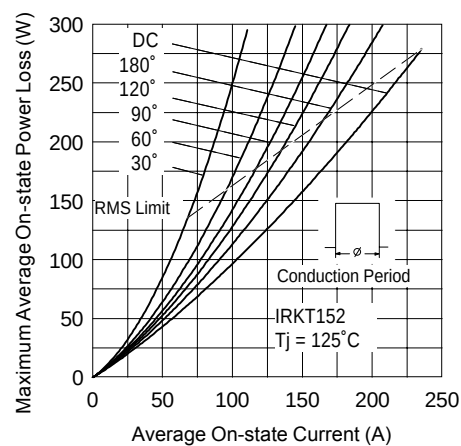


Fig. 4 - Forward Power Loss Characteristics

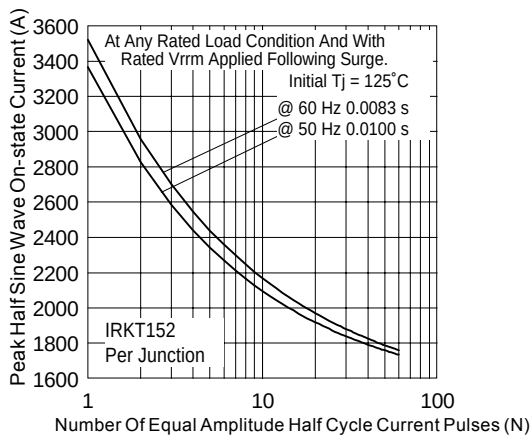


Fig. 5 - Maximum Non-Repetitive Surge Current

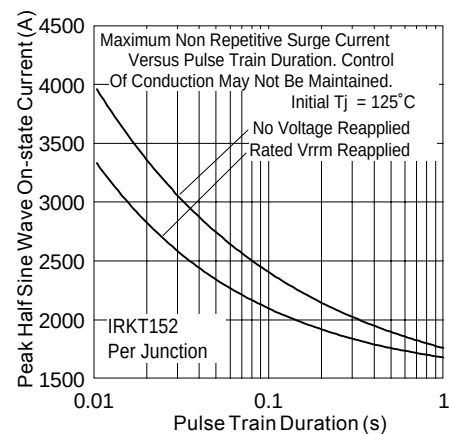


Fig. 6 - Maximum Non-Repetitive Surge Current

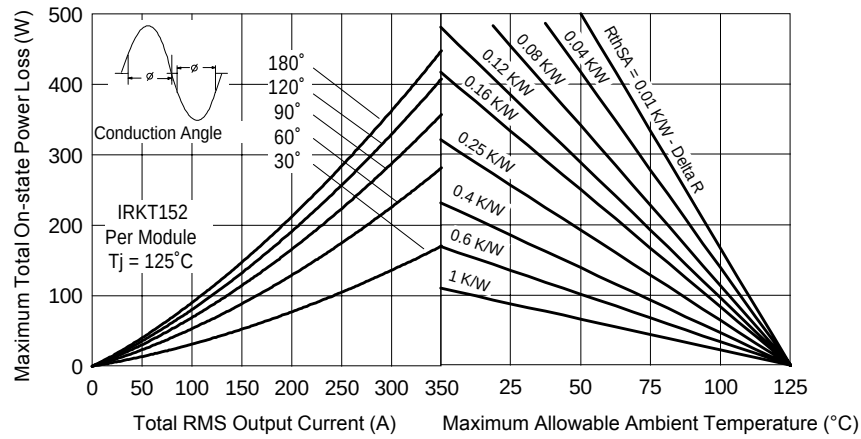


Fig. 7 - On State Power Loss Characteristics

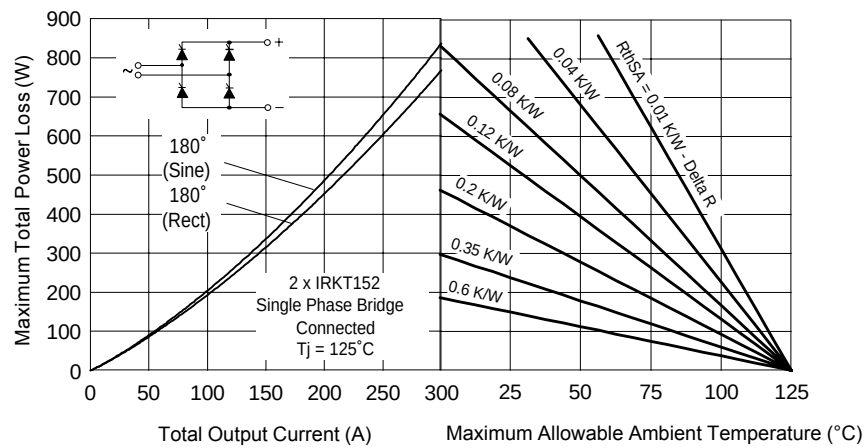


Fig. 8 - On State Power Loss Characteristics

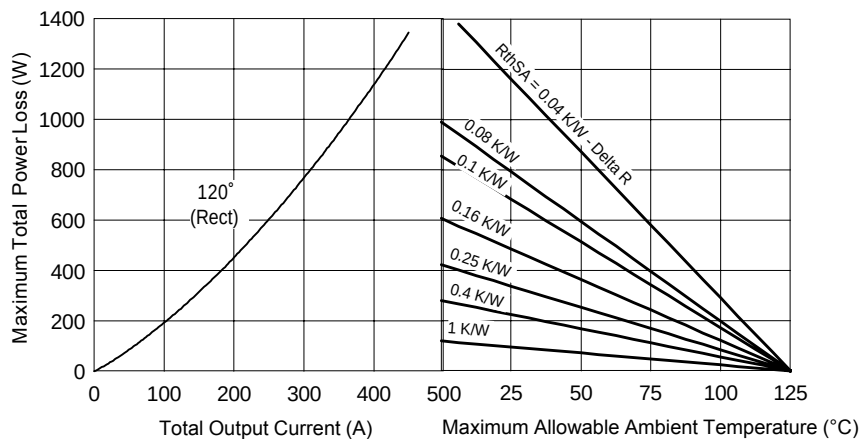


Fig. 9 - On State Power Loss Characteristics

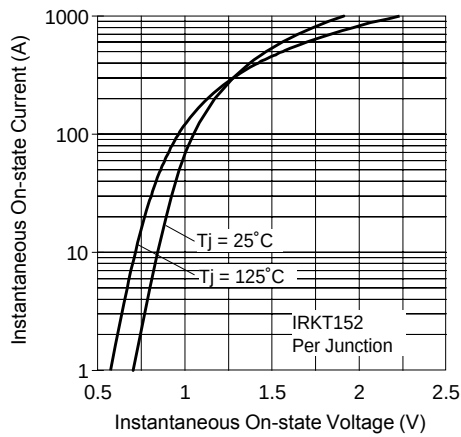


Fig. 10 - On-State Voltage Drop Characteristics

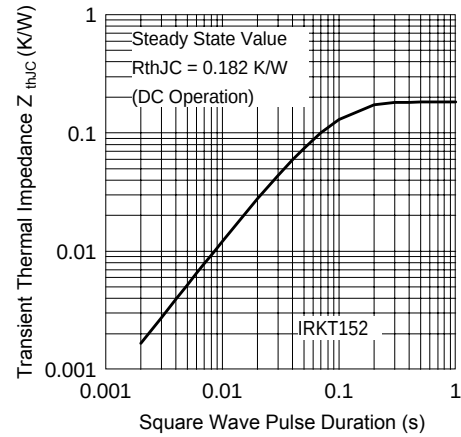


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

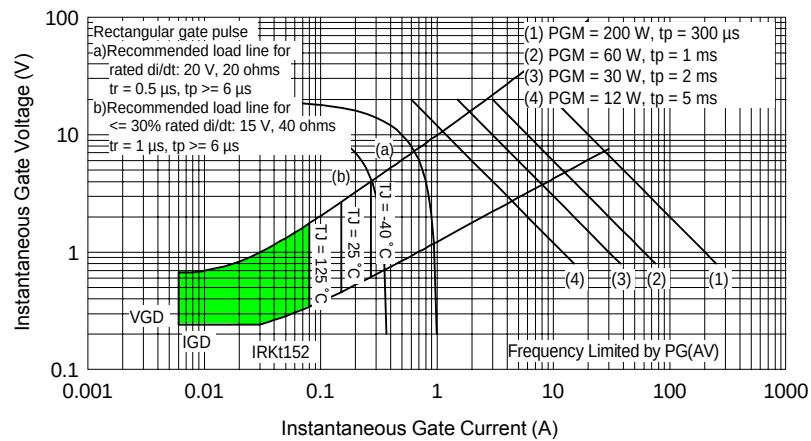


Fig. 12 - Gate Characteristics

Data and specifications subject to change without notice.
This product has been designed and qualified for Multiple Level.
Qualification Standards can be found on IR's Web site.